

Single N-Channel 55 V 3.8 W 63 nC Hexfet Power Mosfet Surface Mount - D2PAK-3

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-263-2
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRFZ44NSTRLPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known

for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

1. Advanced Process Technology
2. Surface Mount (IRFZ44NS)
3. Low-profile through-hole (IRFZ44NL)
4. 175°C Operating Temperature
5. Fast Switching
6. Fully Avalanche Rated

Features

Planar cell structure for wide SOA

Optimized for broadest availability from distribution partners

Product qualification according to JEDEC standard

Silicon optimized for applications switching below <100kHz

Industry standard surface-mount power package

High-current carrying capability package (up to 195 A, die-size dependent)

Capable of being wave-soldered



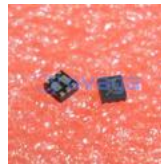


Related Products



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Infineon Technologies Corporation
TSOP-6



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SOIC-8